**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT186A (TO-220F) "full pack" plastic package intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

#### 2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- · Isolated package
- Low holding current for small load currents and lowest EMI at commutation
- · Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate for easy logic level triggering

### 3. Applications

- General purpose motor control
- General purpose switching

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	35	А
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 98$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	4	A
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;} $ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		T2 — T1 G sym051

# 6. Ordering information

**Table 3. Ordering information** 

table 6. Ordering information						
Type number	Package					
	Name	Description	Version			
BT234X-800D	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A			

## 7. Limiting values

### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \le 98$ °C; Fig. 1; Fig. 2; Fig. 3	-	4	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; $t_p = 20 \text{ms}$ ; Fig. 4; Fig. 5	-	35	А
		full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; $t_p = 16.7 \text{ms}$	-	38.5	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	6.1	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 10 mA; T2+ G+	-	50	A/µs
		I <sub>G</sub> = 10 mA; T2+ G-	-	50	A/µs
		I <sub>G</sub> = 10 mA; T2- G-	-	50	A/µs
		I <sub>G</sub> = 20 mA; T2- G+	-	10	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_GM$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C

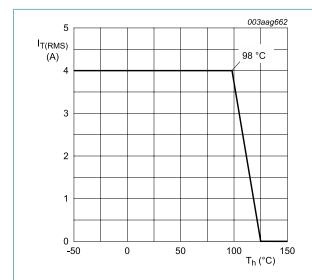


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values

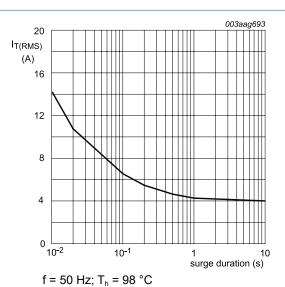


Fig. 2. RMS on-state current as a function of surge duration; maximum values

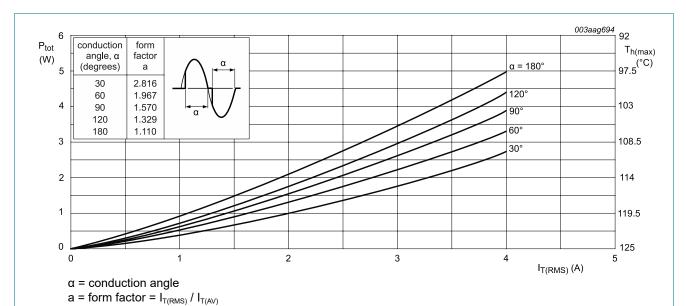


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

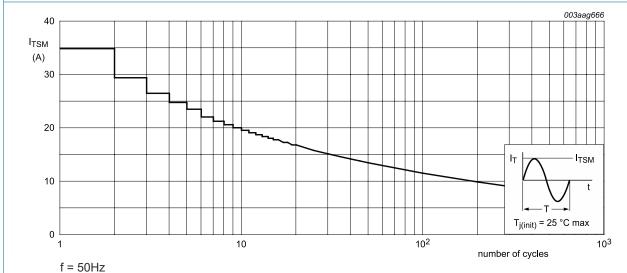
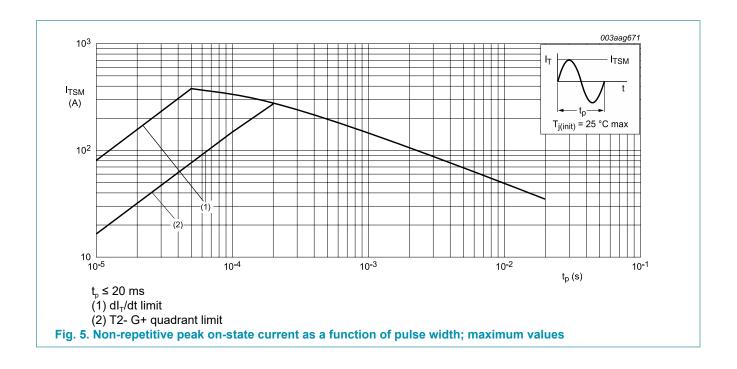


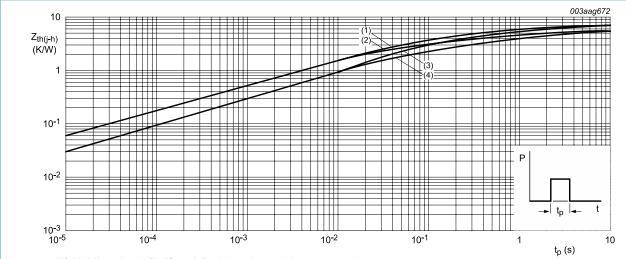
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to	full or half cycle; with heatsink compound; <u>Fig. 6</u>	-	-	5.5	K/W
	heatsink	full or half cycle; without heatsink compound; Fig. 6	-	-	7.2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

#### 9. Isolation characteristics

**Table 6. Isolation characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; R <sub>H</sub> $\leq$ 65 %; T <sub>h</sub> = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

## 10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cl	naracteristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
l <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	10	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G -;$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	15	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	6	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 6 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamio	c characteristics					
dV <sub>□</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	-	50	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D = 400 \text{ V}; I_{T(RMS)} = 4 \text{ A}; dV_{com}/dt = 20 \text{ V/}\mu\text{s}; (snubberless condition);}$ gate open circuit	-	1.2	-	A/ms
<b>t</b> <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 6 \text{ A}; V_D = 800 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

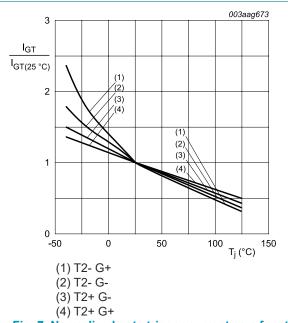


Fig. 7. Normalized gate trigger current as a function of junction temperature

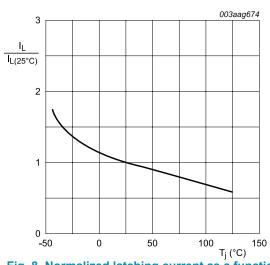


Fig. 8. Normalized latching current as a function of junction temperature

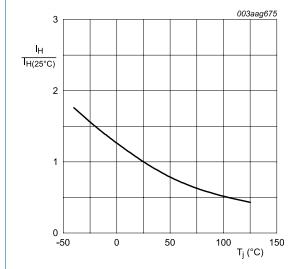
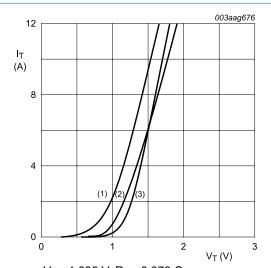


Fig. 9. Normalized holding current as a function of junction temperature



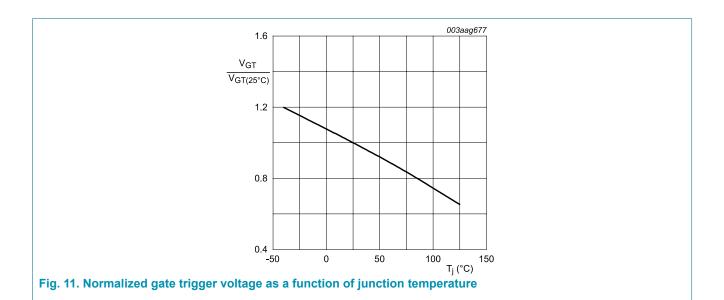
 $V_o$  = 1.035 V;  $R_s$  = 0.078  $\Omega$ 

(1) T<sub>i</sub> = 125 °C; typical values

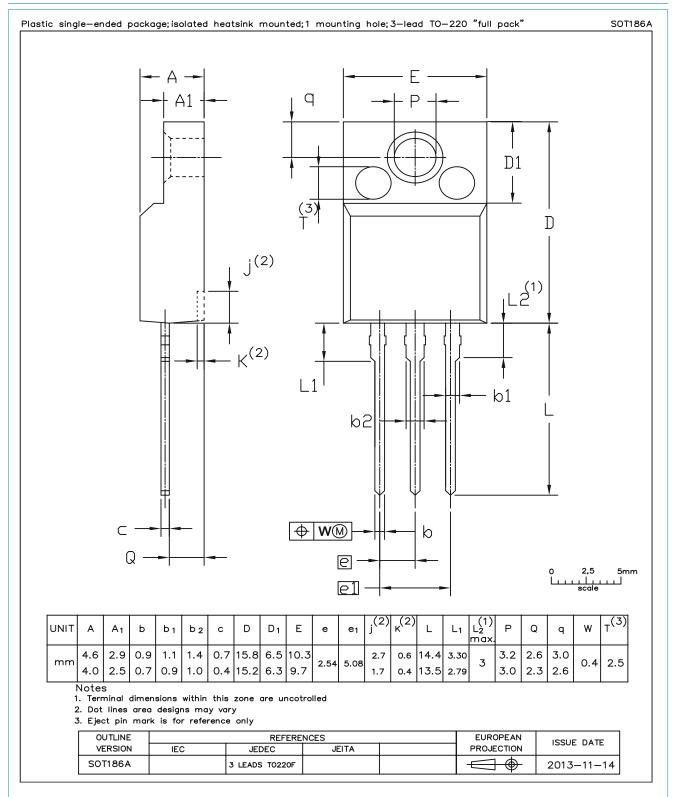
(2) T<sub>i</sub> = 125 °C; maximum values

(3)  $T_i = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage



## 11. Package outline



### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**WeEn Semiconductors** BT234X-800D

**4Q Triac** 

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For more information, please visit: http://www.ween-semi.com
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